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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				<b>Complete if Known</b>	
				<b>Application Number</b>	10/519,700
				<b>Filing Date</b>	09/14/2005
				<b>First Named Inventor</b>	Wade A. Krull
				<b>Group Art Unit</b>	1765
				<b>Examiner Name</b>	Angadi, Maki A
Sheet	1	of	1	<b>Attorney Docket Number</b>	211843-00030

### U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number – Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A1	5,930,634	07-27-1999	Hause Frederick N et al.	
	A2	6,297,109	10-02-2001	Chan Lap et al.	
	A3	5,314,832	05-24-1994	Deleonibus et al.	
	A4	5,828,104	10-27-1998	Mizushima Kazuyuki et al.	
	A5	5,462,884	10-31-1995	Taniguchi Akihisa et al.	
	A6	6,333,229	12-25-2001	Furukawa Toshiharu	

### FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> – Number <sup>4</sup> – Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
	C1	WO 01/43175A	06-14-2001	Infineon Technologies		
	C2	WO 99/65070A	12-16-1999	Philips Svenska		
	C3	EP 0 219 243 A	04-22-1987	Monolithic Memories		
	C4	EP 1 093 149 A	04-18-2001	Axcelis Tech Inc		
	C5	WO 01/69668	09-20-2001	Advanced Micro Devices Inc.		

### OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher city and/or country where published	T <sup>2</sup>
		Schmitz J. ET AL: "Ultra-shallow junction formation by outdiffusion from implanted oxide" 195 <sup>th</sup> Meeting of the Electrochemical Society, 1998, pages 1000-1012, XP002434976 Washington	
		FAIR R: "Physical models of boron diffusion in ultrathin gate oxides" Journal of the Electrochemical Society, vol 144, no. 2, February 1997 (1997-2002), pages 708-717, XP002434977	
Examiner Signature		Date Considered	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds codes of USPTO Patent Documents as [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.